

4W High Power Laser Diode

Preliminary

Description

The SLD343YT has a compatible package, and allows independent thermal and electric design.

It is a high power laser diode that affords easy optical design.

Features

- High-optical power output
Recommended optical power output: $P_o = 4.0W$
- High-optical power density: $4W/200\mu m$
(Emitting line width)

Applications

- Solid state laser excitation
- Medical use
- Material processing
- Measurement

Structure

AlGaAs quantum well structure laser diode

Operating Lifetime

MTTF 10,000H (effective value)
at $P_o = 4.0W$, $T_{th} = 25^\circ C$

Absolute Maximum Ratings ($T_{th} = 25^\circ C$)

- Optical power output P_o 4.4 W
- Reverse voltage V_R LD 2 V
PD 15 V
- Operating temperature (T_{th}) T_{opr} -10 to $+30^\circ C$
- Storage temperature T_{stg} -40 to $+85^\circ C$

Warranty

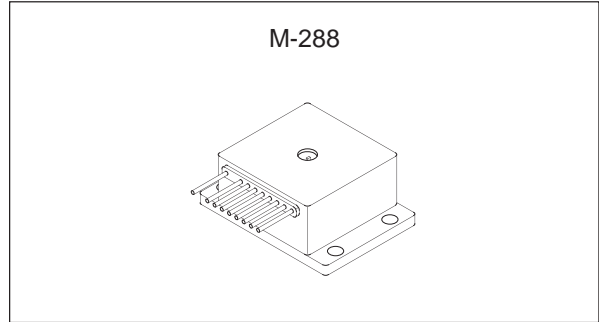
This warranty period shall be 90 days after receipt of the product or 1,000 hours operation time whichever is shorter.

Sony Quality Assurance Department shall analyze any product that fails during said warranty period, and if the analysis results show that the product failed due to material or manufacturing defects on the part of Sony, the product shall be replaced free of charge.

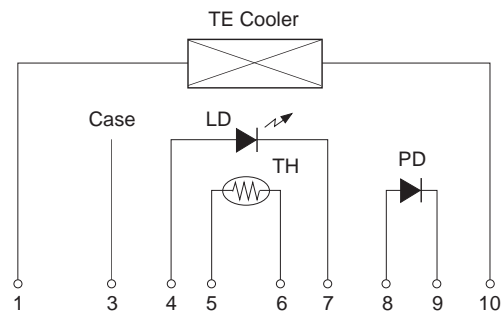
Laser diodes naturally have differing lifetimes which follow a Weibull distribution.

Special warranties are also available.

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Equivalent Circuit



Pin Configuration (Top View)

No.	Function
1	TE cooler (negative)
2	—
3	Case
4	Laser diode (anode)
5	Thermistor
6	Thermistor
7	Laser diode (cathode)
8	Photo diode (anode)
9	Photo diode (cathode)
10	TE cooler (positive)

Electrical and Optical Characteristics

(Tth = Thermistor temperature, Tth = 25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Threshold current	Ith			1.0	2.0	A	
Operating current	Iop	PO = 4.0W		4.6	6.5	A	
Operating voltage	Vop	PO = 4.0W		2.0	3.0	V	
Wavelength*	λ_P	PO = 4.0W	790		840	nm	
Radiation angle	Perpendicular	PO = 4.0W	10	23	35	degree	
	Parallel		5	10	15	degree	
Positional accuracy	Position	PO = 4.0W			±100	µm	
	Angle		$\Delta\phi_{\perp}$			±3	degree
			$\Delta\phi_{//}$			±4	degree
Differential efficiency	η_D	PO = 4.0W	0.5	1.1	1.5	W/A	
Monitor current	Imon	PO = 4.0W VR = 10V	0.2	1.0	4.0	mA	
Thermistor resistance	Rth	Tth = 25°C		10		kΩ	

*** Wavelength Selection Classification**

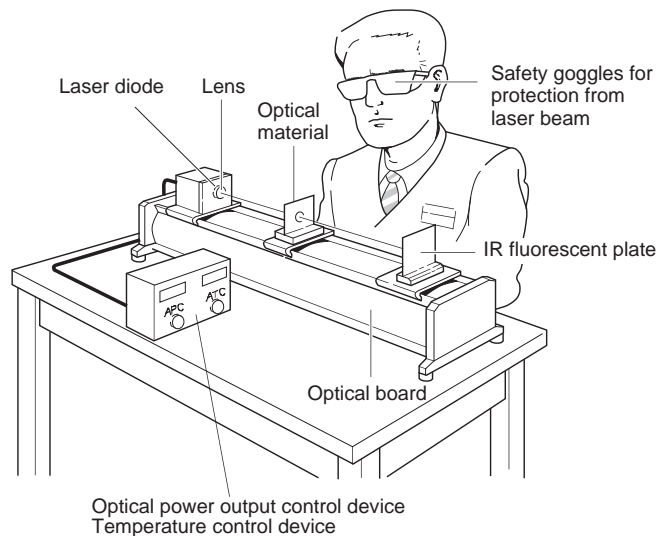
Type	Wavelength (nm)
SLD343YT-1	795 ± 5
SLD343YT-2	810 ± 10
SLD343YT-3	830 ± 10

Type	Wavelength (nm)
SLD343YT-21	798 ± 3
SLD343YT-24	807 ± 3
SLD343YT-25	810 ± 3

Handling Precautions

Eye protection against laser beams

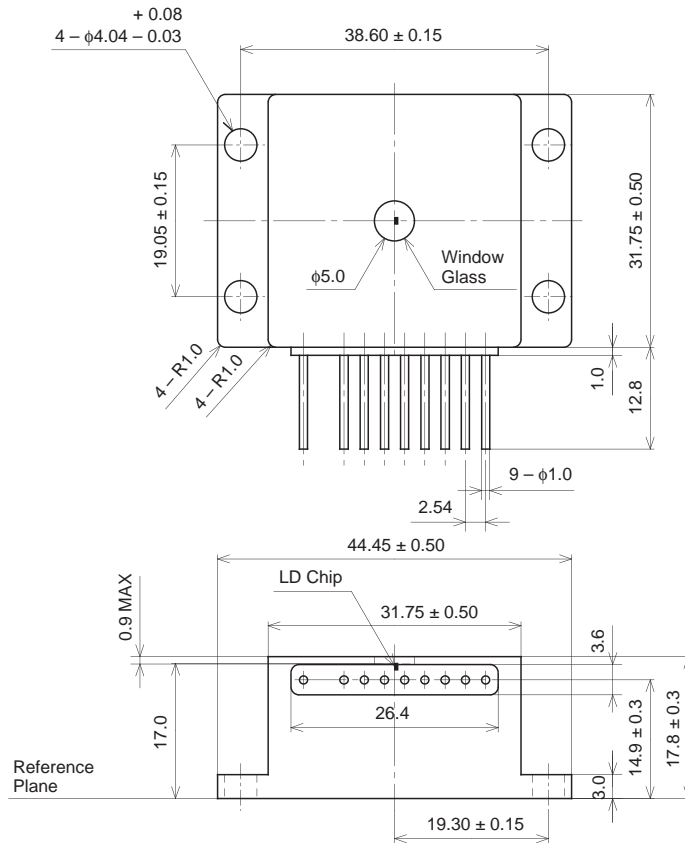
The optical output of laser diodes ranges from several mW to 10W. However the optical power density of the laser beam at the diode chip reaches 1.5MW/cm². Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.



Package Outline

Unit: mm

M-288



SONY CODE	M-288
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE WEIGHT	150g
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